

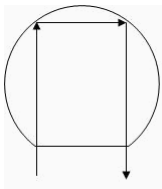
Part Number

Customer

| Category      |      | Parameter                                       | Specification                     | Measurement Method          |
|---------------|------|---|-----------------------------------|-----------------------------|
| OverallWafer  | 1.0  | Diameter  | 100.00 +/- 0.50 mm                |                             |
|               | 2.0  | Primary Flat Orientation                        | {110} +/- 1.0 degree              | Wafer Vendor                |
|               | 3.0  | Primary Flat Length                             | 32.50 +/- 2.50 mm                 | Wafer Vendor                |
|               | 4.0  | Secondary Flat Orientation                      | none / semi std                   |                             |
|               | 5.0  | Overall Thickness                               | 342.00 +/- 7.00 µm                | ADE, 100%                   |
|               | 6.0  | Total Thickness Variation (TTV)                 | <5.00µm                           | Guaranteed by Process       |
|               | 7.0  | Bow   | <60.00µm                          | ADE to ASTM F534, 20%       |
|               | 8.0  | Warp  | <60.00µm                          | ADE to ASTM F657, 20%       |
|               | 9.0  | Edge Chips                                      | 0                                 | Bright Light, 100% (note 2) |
|               | 10.0 | Edge Exclusion                                  | 5mm                               |                             |
| HandleSilicon | 11.0 | Handle Growth Method                            | CZ                                | Wafer Vendor                |
|               | 12.0 | Handle Orientation                              | {100} +/- 1.0 degree              | Wafer Vendor                |
|               | 13.0 | Handle Thickness                                | 300.00 +/- 5.00 µm                | ADE, 100%                   |
|               | 14.0 | Handle Doping Type                              | P                                 | Wafer Vendor                |
|               | 15.0 | Handle Dopant                                   | Boron                             | Wafer Vendor                |
|               | 16.0 | Handle Resistivity                              | 0.05 ~ 0.5 Ohmcm                  | Wafer Vendor                |
|               | 17.0 | Backside Finish                                 | Polished with oxide and lasermark | Wafer Vendor                |
| BuriedOxide   | 18.0 | Oxide Type                                      | Thermal                           |                             |
|               | 19.0 | Oxide Thickness                                 | 20,000.00 +/- 1,000.00 Å          | Nanospec centre point, 4%   |
|               | 20.0 | Oxide formed on                                 | Handle and/or device wafer        |                             |
| DeviceSilicon | 21.0 | Device Growth Method                            | CZ                                | Wafer Vendor                |
|               | 22.0 | Device Orientation                              | {100} +/- 1.0 degree              | Wafer Vendor                |
|               | 23.0 | Nominal Thickness                               | 40.00 +/- 1.00 µm                 | ADE Single point, 100%      |
|               | 24.0 | Distance to device silicon edge from wafer edge | <= 2mm                            | Typical by Process          |
|               | 25.0 | Device Doping Type                              | P                                 | Wafer Vendor                |
|               | 26.0 | Device Dopant                                   | Boron                             | Wafer Vendor                |
|               | 27.0 | Device Resistivity                              | <0.0015 Ohmcm                     | Wafer Vendor                |
|               | 28.0 | Voids   | 0                                 | Bright Light, 100% (note 2) |
|               | 29.0 | Scratches                                       | 0                                 | Bright Light, 100% (note 2) |
|               | 30.0 | Haze  | none                              | Bright Light, 100% (note 2) |

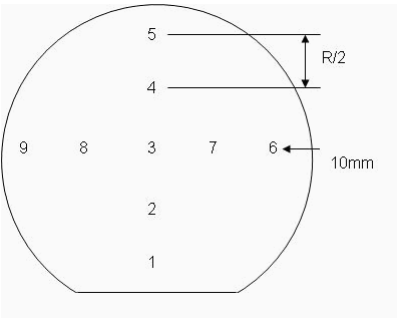
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|-------------|----------|
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|-------------|----------|

| Category | Parameter | Specification | Measurement Method |
|----------|-----------|---------------|--------------------|
|----------|-----------|---------------|--------------------|

|                   |  |   |   |
|-------------------|--|---|---|
| Shipping Details  | Wafer per box :  | Max 25  |  |
|                   | Packaging :  | Taped Polypropylene Wafer Box<br>Empak, Ultrapak, 100.00mm<br>Antistatic Double Bagging |   |
|                   | Lot Shipment Data  | Device Thickness<br>Bow / Warp Data<br>Handle and SOI Thickness                         |   |
| Explanatory Notes | 1. Microscope inspection performed using microscope scan as below. 5x objective. |   |   |

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information